Dedication

To my parents

Kee-Ho Song

and

Soon-G Lee
Acknowledgments

I would like to first thank Dr. S. B. Desu for his continual guidance and endless patience during my entire work in Virginia Tech. I am grateful to him for allowing me to follow my own research interests while providing me with essential advice. Without his encouragement and support, I would have not finished this work. I also would like to express my sincere appreciation to my advisory committee members Dr. Bill Reynolds, Dr. William Curtin, Dr. Alex Huang, and Dr. G. Q. Lu for providing invaluable suggestions and remarks in their already heavy loads of responsibility. I wish to thank Dr. Hyo-duk Nam and Dr. Sa-gong Geon for their caring and concerns about my research and living in Blacksburg.

It was also lots of fun to work with lab colleagues. I absolutely enjoyed working with Ryu, Sukku, Vedula, Chandra, Vikto, Shanky, Dr. Bhutt, June Key Lee, Prof. Alouk, Prof. Lee, Zhu, Xubai, Dr. Hwang, Dr. Cho, and Dr. Joshi. I also express my greatest thanks to my wonderful long-time roommate, Younsoo Kang, and new mate, Hongman Kim. My sincere thanks go to many friends for their support and encouragement. My life in Blacksburg was full of fun especially due to Keangyoung Kang, Kyeahwan Oh, Kyeangsik Kang, Yuri Lee, Joonwon Choi, Dr. Jae-Cheul Bang and other Korean colleagues.

I dedicate this small achievement to my parents, my brother and his new full-time partner, and my special friend, Namyoung Park. My deepest appreciation is expressed to her for her love, understanding, and inspiration. Without their blessings and encouragement, I would not have been able to finish this work. I know it is impossible to sufficiently describe their supports and love that they have shown me over the years.
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